

Silicon Power Schottky Diode

 $V_{RRM} = 20\text{ V} - 100\text{ V}$
 $I_F = 400\text{ A}$

Features

- High Surge Capability
- Types up to 100 V V_{RRM}

Twin Tower Package

Maximum ratings, at $T_j = 25\text{ °C}$, unless otherwise specified ("R" devices have leads reversed)

Parameter	Symbol	Conditions	MBR40020CT (R)	MBR40030CT (R)	MBR40035CT (R)	MBR40040CT (R)	Unit
Repetitive peak reverse voltage	V_{RRM}		20	30	35	40	V
RMS reverse voltage	V_{RMS}		14	21	25	28	V
DC blocking voltage	V_{DC}		20	30	35	40	V
Continuous forward current	I_F	$T_C \leq 125\text{ °C}$	400	400	400	400	A
Surge non-repetitive forward current, Half Sine Wave	$I_{F,SM}$	$T_C = 25\text{ °C}$, $t_p = 8.3\text{ ms}$	3000	3000	3000	3000	A
Operating temperature	T_j		-40 to 175	-40 to 175	-40 to 175	-40 to 175	°C
Storage temperature	T_{stg}		-40 to 175	-40 to 175	-40 to 175	-40 to 175	°C

Electrical characteristics, at $T_j = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Conditions	MBR40020CT (R)	MBR40030CT (R)	MBR40035CT (R)	MBR40040CT (R)	Unit
Diode forward voltage	V_F	$I_F = 200\text{ A}$, $T_j = 25\text{ °C}$	0.65	0.65	0.65	0.65	V
Reverse current	I_R	$V_R = 20\text{ V}$, $T_j = 25\text{ °C}$	5	5	5	5	mA
		$V_R = 20\text{ V}$, $T_j = 125\text{ °C}$	200	200	200	200	

Thermal characteristics

Parameter	Symbol	Conditions	MBR40020CT (R)	MBR40030CT (R)	MBR40035CT (R)	MBR40040CT (R)	Unit
Thermal resistance, junction - case	R_{thJC}		0.35	0.35	0.35	0.35	°C/W

Figure .1-Typical Forward Characteristics

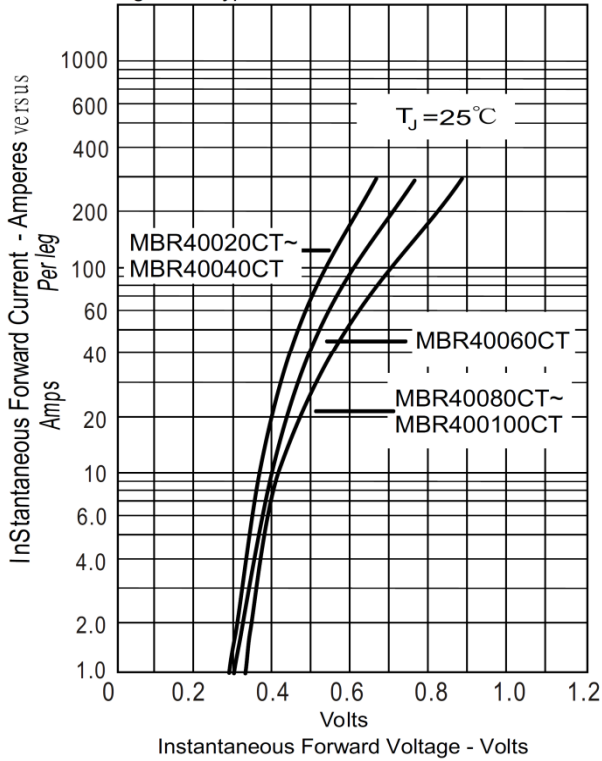


Figure .2- Forward Derating Curve

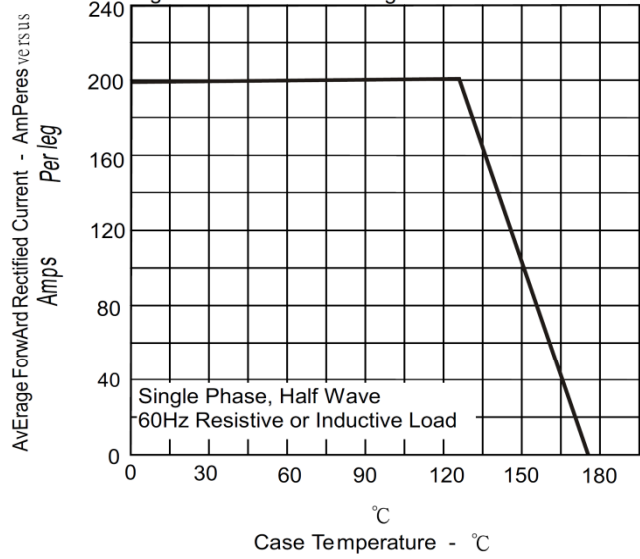


Figure.3-Peak Forward Surge Current

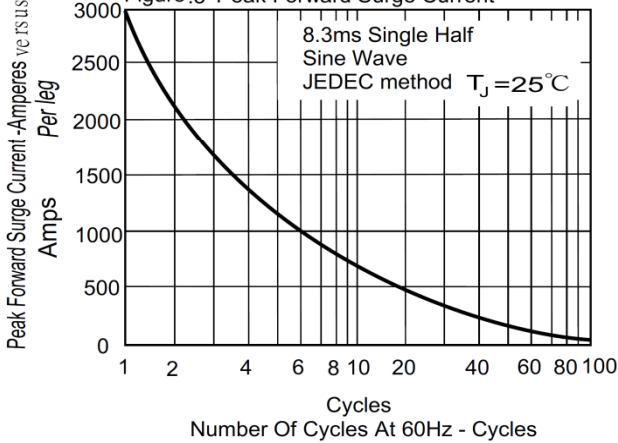


Figure .4- Typical Reverse Characteristics

